

N-channel 50 V, 0.90 mOhm, 410 A logic level Application Specific MOSFET in LFPAK88

15 March 2022

**Product data sheet** 

### 1. General description

410 Amp continuous current, logic level gate drive N-channel enhancement mode MOSFET in 175 °C LFPAK88 package. Part of the ASFETs for Battery Isolation and DC Motor control family and using Nexperia's unique "SchottkyPlus" technology delivers high efficiency and low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. The ASFET is particularly suited to 36 V battery powered applications requiring strong avalanche capability, linear mode performance, use at high switching frequencies, and also safe and reliable switching at high load-current.

## 2. Features and benefits

- 410 Amp continuous current capability
- LFPAK88 (8 x 8 mm) LFPAK-style low-stress exposed lead-frame for ultimate reliability, optimum soldering and easy solder-joint inspection
- Copper-clip and solder die attach for low package inductance and resistance, and high I<sub>D(max)</sub> rating
- Ideal replacement for D2PAK and 10 x 12 mm leadless package types
- Qualified to 175 °C
- Avalanche rated, 100 % tested
- Low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high efficiency, especially at higher switching frequencies
- Superfast switching with soft body-diode recovery for low-spiking and ringing, recommended for low EMI designs
- Unique "SchottkyPlus" technology for Schottky-like switching performance and low I<sub>DSS</sub> leakage
- Narrow V<sub>GS(th)</sub> rating for easy paralleling and improved current sharing
- Very strong linear-mode / safe operating area characteristics for safe and reliable switching at high-current conditions

### 3. Applications

- Brushless DC motor control
- Synchronous rectifier in high-power AC-to-DC applications, e.g. server power supplies
- Battery protection
- eFuse and load switch
- Hotswap / in-rush current management
- 10 cell lithium-ion battery applications (36 V 42 V)

## 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	50	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	410	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	375	W
Tj	junction temperature			-55	-	175	°C

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	0.7	0.9	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	0.8	1.01	mΩ
Dynamic ch	naracteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 25 V; $V_{GS}$ = 4.5 V;	-	26	57	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13	-	112	174	nC

[1] 410A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

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Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		D
3	S	source	0	
4	S	source		G_(片五)
mb	D	mounting base; connected to drain		mbb076 S
			LFPAK88 (SOT1235)	

### 6. Ordering information

### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMNR90-50SLH	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235			

### 7. Marking

Table 4. Marking codes					
Type number	Marking code				
PSMNR90-50SLH	XH90L50S				

## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	50	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤  T <sub>j</sub> ≤  175 °C; R <sub>GS</sub> = 20 kΩ	-	50	V
V <sub>GS</sub>	gate-source voltage		-20	20	V

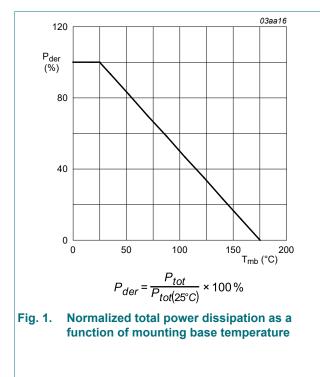
PSMNR90-50SLH

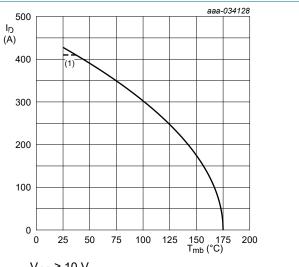
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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	375	W
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	410	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	302	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	1711	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	410	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1711	А
Avalanche r	uggedness					_
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 50 A; V <sub>sup</sub> ≤ 50 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 1.8 ms	[2]	-	3	J
		$I_D = 25$ A; $V_{sup} \le 50$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped; $t_p = 9.1$ ms	[2]	-	7.4	J
I <sub>AS</sub>	non-repetitive avalanche current		[2]	-	175	A

[1] 410A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test



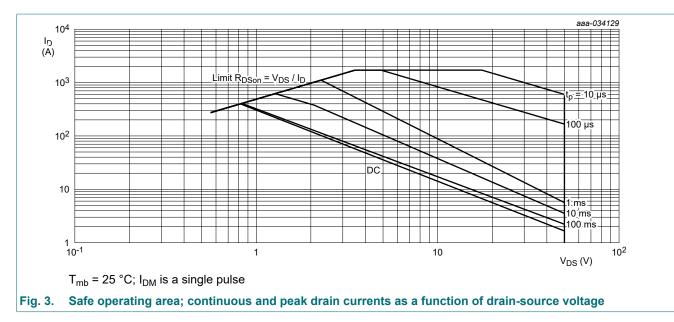


 $V_{GS} \ge 10 V$ 

(1) 410A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



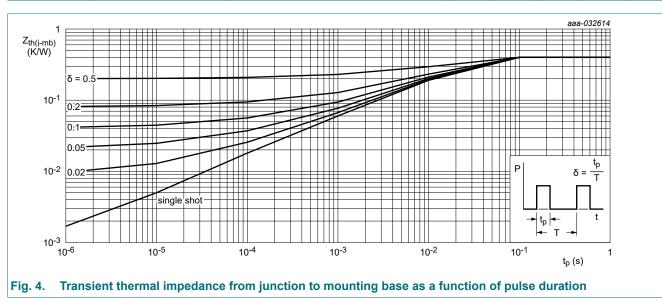
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### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.35	0.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from	Fig. 5	-	35	-	K/W
	junction to ambient	Fig. 6	-	70	-	K/W



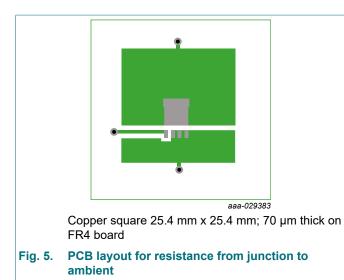


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### Nexperia

## PSMNR90-50SLH

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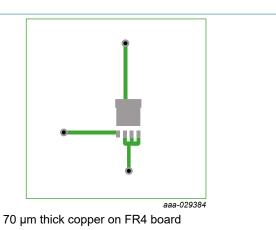


Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	50	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	45	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1.2	1.6	2.2	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-4.9	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	7	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	0.7	0.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; <u>Fig. 11</u>	-	-	1.82	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	0.8	1.01	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11	-	-	2.03	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.4	1	2.5	Ω
Dynamic cha	racteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 25 V; $V_{GS}$ = 4.5 V; Fig. 12; Fig. 13	-	112	174	nC
		$I_D$ = 25 A; $V_{DS}$ = 25 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	247	383	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	139	-	nC

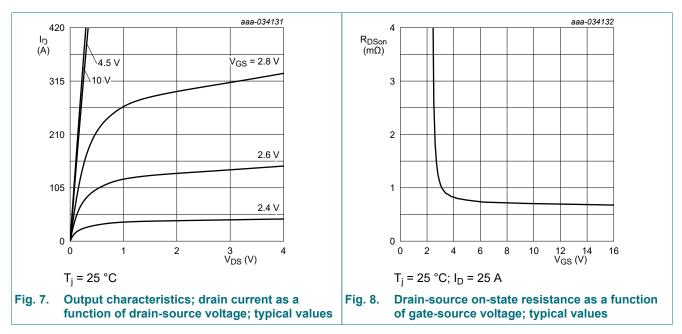
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 4.5 V;		-	34	51	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13		-	24	36	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge	_		-	11	17	nC
Q <sub>GD</sub>	gate-drain charge	-		-	26	57	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	2.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	17829	24961	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		-	1554	2176	pF
C <sub>rss</sub>	reverse transfer capacitance			-	485	1163	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 25 V; R <sub>L</sub> = 1.1 Ω; V <sub>GS</sub> = 4.5 V;		-	74	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$		-	66	-	ns
t <sub>d(off)</sub>	turn-off delay time	_		-	134	-	ns
t <sub>f</sub>	fall time	-		-	55	-	ns
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	82	-	nC
Source-drai	in diode	1					_
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	0.73	1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	48	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; <u>Fig. 16</u>	[1]	-	66	-	nC
t <sub>a</sub>	reverse recovery rise time			-	29	-	ns
t <sub>b</sub>	reverse recovery fall time			-	19	-	ns

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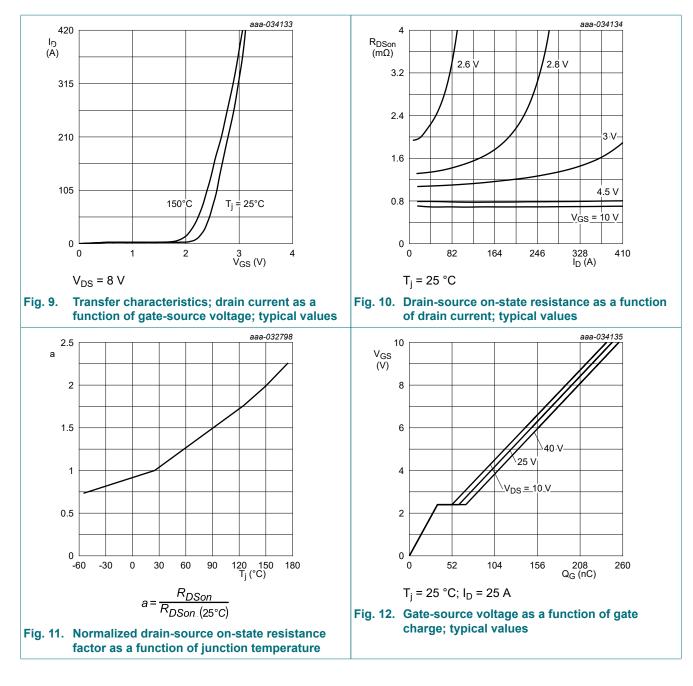
[1] includes capacitive recovery



PSMNR90-50SLH

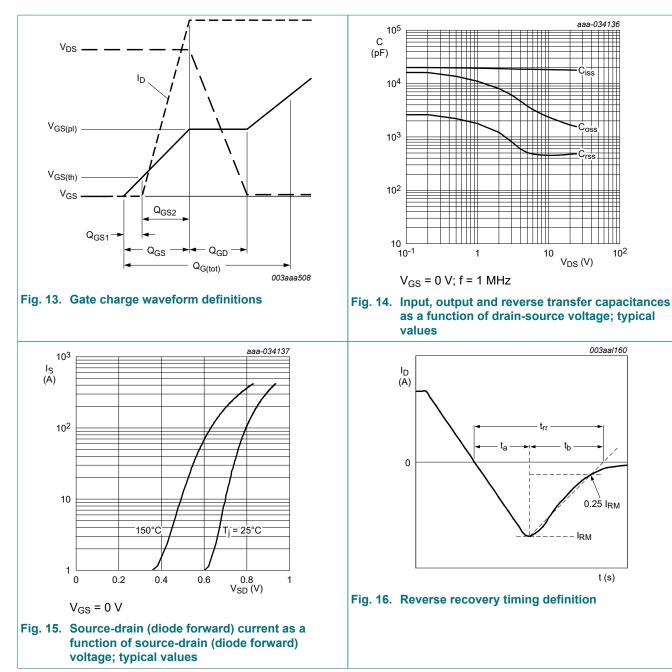
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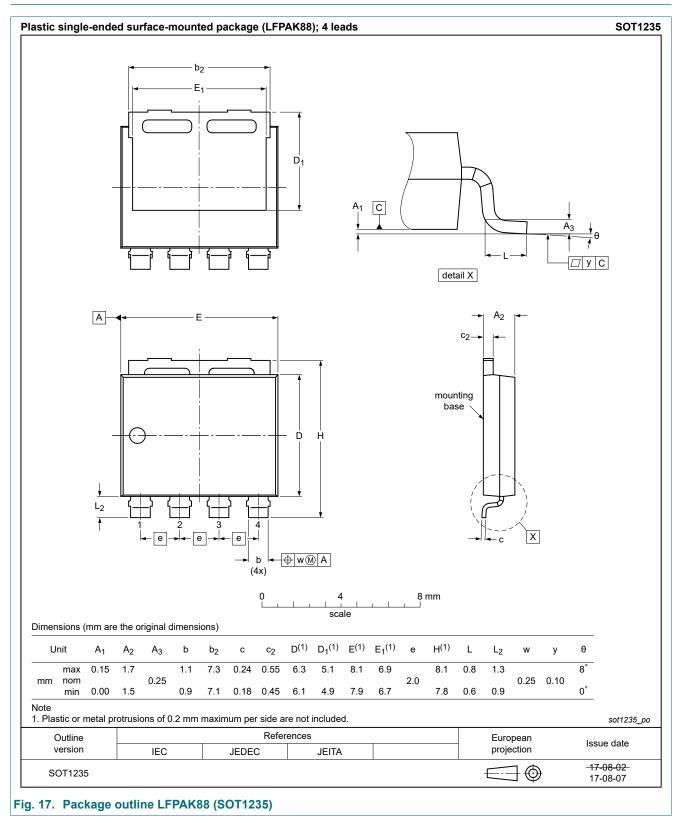
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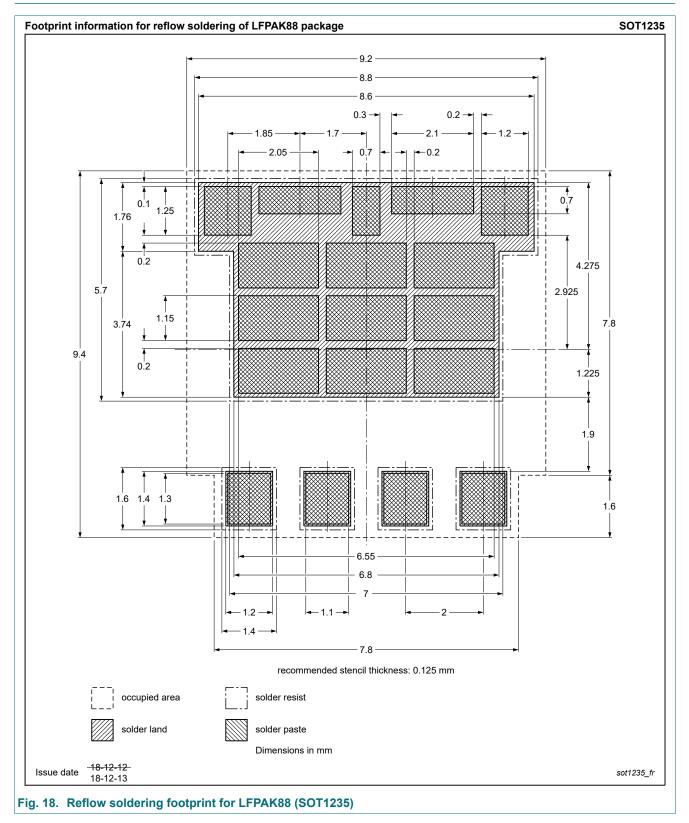


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## 11. Package outline



## 12. Soldering



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## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## Contents

	O a manual also a ministra m	
1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	4
10.	. Characteristics	5
11.	. Package outline	9
12.	. Soldering	10
13.	. Legal information	11

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